



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FIS920030371US1

Application Number

10/708,378

Applicant(s)

Zhu, et al.

Filing Date

2-27-04

Group Art Unit

2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
W		4,952,524	8-28-90	Lee, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
W		US 2002/0086472	7-4-02	Roberds, et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
W		JP64-76755	03-1989	Japan				

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

W		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
W		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		4,958,213	9-18-90	Eklund, et al.			
		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
W		5,108,843	4-28-92	Ohtaka, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
W		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeh, et al.			
W		US 2003/0040158 A1	2-27-03	Saitoh			

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							YES	NO

OTHER DOCUMENTS		<i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>
W		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress." International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
W		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

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M		5,134,085	7-28-92	Gilgen, et al.	1	1		
		5,310,446	5-10-94	Konishi, et al.	1	1		
		5,354,695	10-11-94	Leedy	1	1		
		5,371,399	12-6-94	Burroughes, et al.	1	1		
M		5,391,510	2-21-95	Hsu, et al.	1	1		
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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
M		US 2003/0057184 A1	3-27-03	Yu, et al.	1	1		
M		US 2003/0067035 A1	4-10-03	Tews, et al.	1	1		
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
M		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.						
M		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.						
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M Jm ✓ M				5-15-05				
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W		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
W		5,565,697	10-15-96	Asakawa, et al.			

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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

W		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
W		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

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W J M

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				2-27-04		2818		
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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
m		5,571,741	11-5-96	Leedy				
		5,592,007	1-7-97	Leedy				
		5,592,018	1-7-97	Leedy				
		5,670,798	9-23-97	Schetzina				
m		5,679,965	10-21-97	Schetzina				
U.S. PATENT APPLICATION PUBLICATIONS								
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OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
m		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.						
m		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.						
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m m ✓ m				8-15-05				
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2-27-04				2818				
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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
W		5,683,934	11-4-97	Candelaria				
		5,840,593	11-24-98	Leedy				
		5,861,651	1-19-99	Brasen, et al.				
		5,880,040	3-9-99	Sun, et al.				
W		5,940,716	8-17-99	Jin, et al.				
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OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
W		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.						
W		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.						
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Wm ✓ M				8-15-05				
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				Filing Date 2-27-04		Group Art Unit 2818		
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
M		5,940,736	8-17-99	Brady, et al.				
		5,946,559	8-31-99	Leedy				
		5,960,297	9-28-99	Saki				
		5,989,978	11-23-99	Peidous				
M		6,008,126	12-28-99	Leedy				
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OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
M		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.						
M		H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.						
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M/jm ✓ M				5-15-05				
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2-27-04				2818				
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
NW		6,025,280	2-15-00	Brady, et al.				
		6,046,464	4-4-00	Schetzina				
		6,066,545	5-23-00	Doshi, et al.				
		6,090,684	7-18-00	Ishitsuka, et al.				
NW		6,107,143	8-22-00	Park, et al.				
U.S. PATENT APPLICATION PUBLICATIONS								
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OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
NW		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.						
NW		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.						
EXAMINER				DATE CONSIDERED				
Nym ✓ NY				8-15-05				
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2-27-04				2818				
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HW		6,117,722	9-12-00	Wuu, et al.				
		6,133,071	10-17-00	Nagai				
		6,165,383	12-26-00	Chou				
		6,221,735	4-24-01	Manley, et al.				
HW		6,228,694	5-8-01	Doyle, et al.				
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Mjm ✓ mj				5-15-05				
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NT		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
NT		6,274,444	8-14-01	Wang			

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M		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
M		6,361,885	3-26-02	Chou			

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NW		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
NW		6,406,973	6-18-02	Lee			

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PP		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
PP		6,498,358	12-24-02	Lach, et al.			

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NP		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
NP		6,531,369	3-11-03	Ozkan, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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NW		6,531,740	3-11-03	Bosco, et al.			
I		6,621,392	9-16-03	Volant, et al.			
NW		6,635,506	10-21-03	Volant, et al.			

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